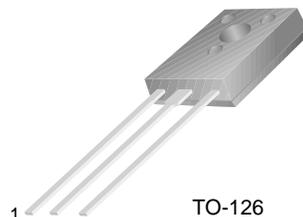


**High Speed
High Voltage Switching Industrial Use**



TO-126
1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 500 | V |
| V_{CEO} | Collector-Emitter Voltage | 400 | V |
| V_{EBO} | Emitter-Base Voltage | 7 | V |
| I_C | Collector Current (DC) | 0.5 | A |
| I_{CP} | *Collector Current (Pulse) | 1 | A |
| I_B | Base Current (DC) | 0.25 | A |
| P_C | Collector Dissipation ($T_a=25^\circ\text{C}$) | 1 | W |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 10 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 55 ~ 150 | $^\circ\text{C}$ |

* $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 10\%$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|------------------------|--|---|----------|------|---------------|
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | $I_C = 0.3\text{A}$, $I_{B1} = 0.06\text{A}$, $L = 10\text{mH}$ | 400 | | V |
| $V_{CEX(sus)1}$ | Collector-Emitter Sustaining Voltage | $I_C = 0.3\text{A}$, $I_{B1} = -I_{B2} = 0.06\text{A}$ $V_{BE(off)} = -5\text{V}$, $L = 10\text{mH}$, Clamped | 450 | | V |
| $V_{CEX(sus)2}$ | Collector-Emitter Sustaining Voltage | $I_C = 0.6\text{A}$, $I_{B1} = 0.2\text{A}$, $I_{B2} = -0.06\text{A}$ $V_{BE(off)} = -5\text{V}$, $L = 10\text{mH}$, Clamped | 400 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 400\text{V}$, $I_E = 0$ | | 10 | μA |
| I_{CER} | Collector Cut-off Current | $V_{CE} = 400\text{V}$, $R_{BE} = 51\Omega$, $T_C = 125^\circ\text{C}$ | | 1 | mA |
| I_{CEX1} | Collector Cut-off Current | $V_{CE} = 400\text{V}$, $R_{BE(off)} = -1.5\text{V}$ | | 10 | μA |
| I_{CEX2} | Collector Cut-off Current | $V_{CE} = 400\text{V}$, $R_{BE(off)} = -1.5\text{V}$ @ $T_C = 125^\circ\text{C}$ | | 1 | mA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 5\text{V}$, $I_C = 0$ | | 10 | μA |
| h_{FE1} h_{FE2} | * DC Current Gain | $V_{CE} = 5\text{V}$, $I_C = 0.05\text{A}$ $V_{CE} = 5\text{V}$, $I_C = 0.3\text{A}$ | 20 10 | 80 | |
| $V_{CE(sat)}$ | * Collector-Emitter Saturation Voltage | $I_C = 0.3\text{A}$, $I_B = 0.06\text{A}$ | | 1 | V |
| $V_{BE(sat)}$ | * Base-Emitter Saturation Voltage | $I_C = 0.3\text{A}$, $I_B = 0.06\text{A}$ | | 2 | V |
| t_{ON} | Turn ON Time | $V_{CC} = 150\text{V}$, $I_C = 0.3\text{A}$ | | 1 | μs |
| t_{STG} | Storage Time | $I_{B1} = -I_{B2} = 0.06\text{A}$, $R_L = 500\Omega$ $PW = 50\mu\text{s}$, Duty Cycle $\leq 2\%$ | | 2.5 | μs |
| t_F | Fall Time | | | 1 | μs |

* Pulse Test: $PW \leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$ Pulsed

h_{FE} Classification

| Classification | R | O | Y |
|----------------|---------|---------|---------|
| h_{FE1} | 20 ~ 40 | 30 ~ 60 | 40 ~ 80 |

Typical Characteristics

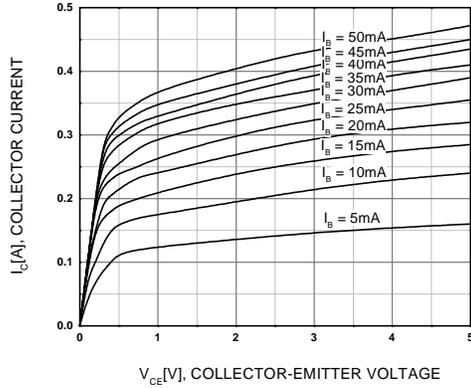


Figure 1. Static Characteristic

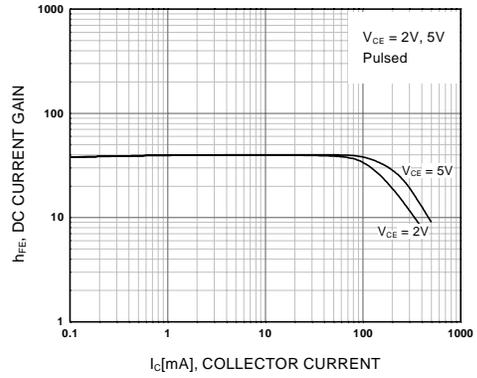


Figure 2. DC current Gain

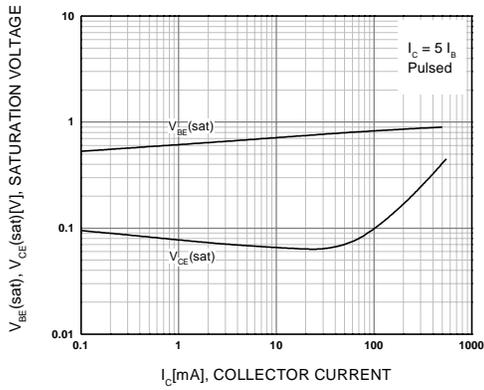


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

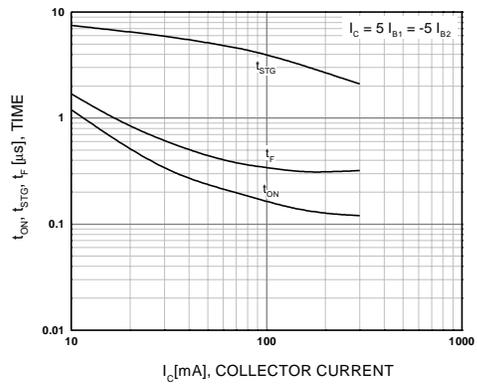


Figure 4. Switching Time

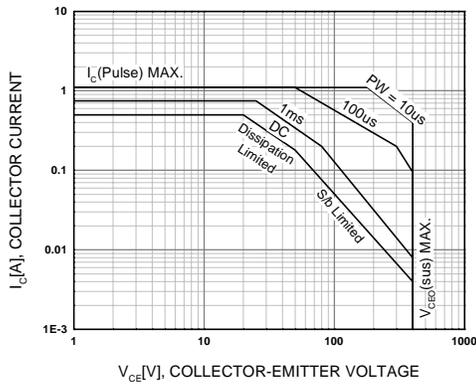


Figure 5. Safe Operating Area

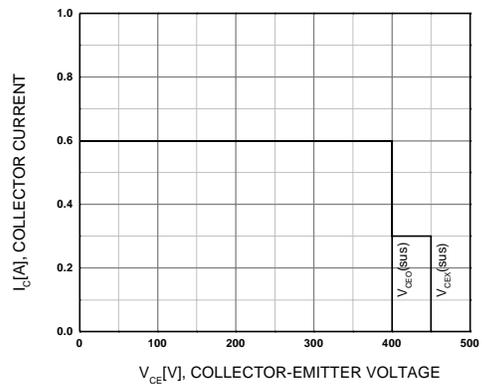


Figure 6. Reverse Bias Safe Operating Area

Typical Characteristics (Continued)

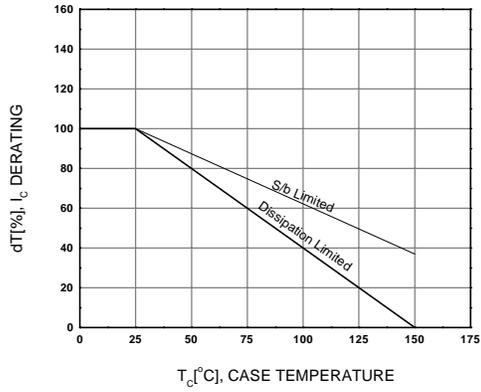


Figure 7. Derating Curve of Safe Operating Area

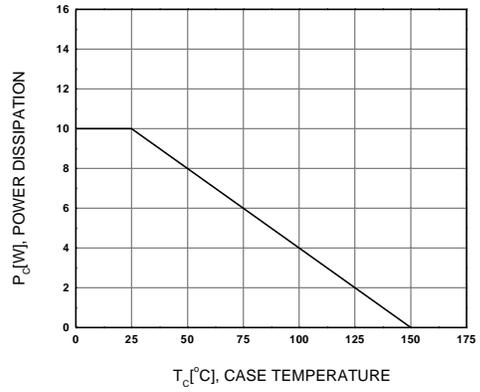
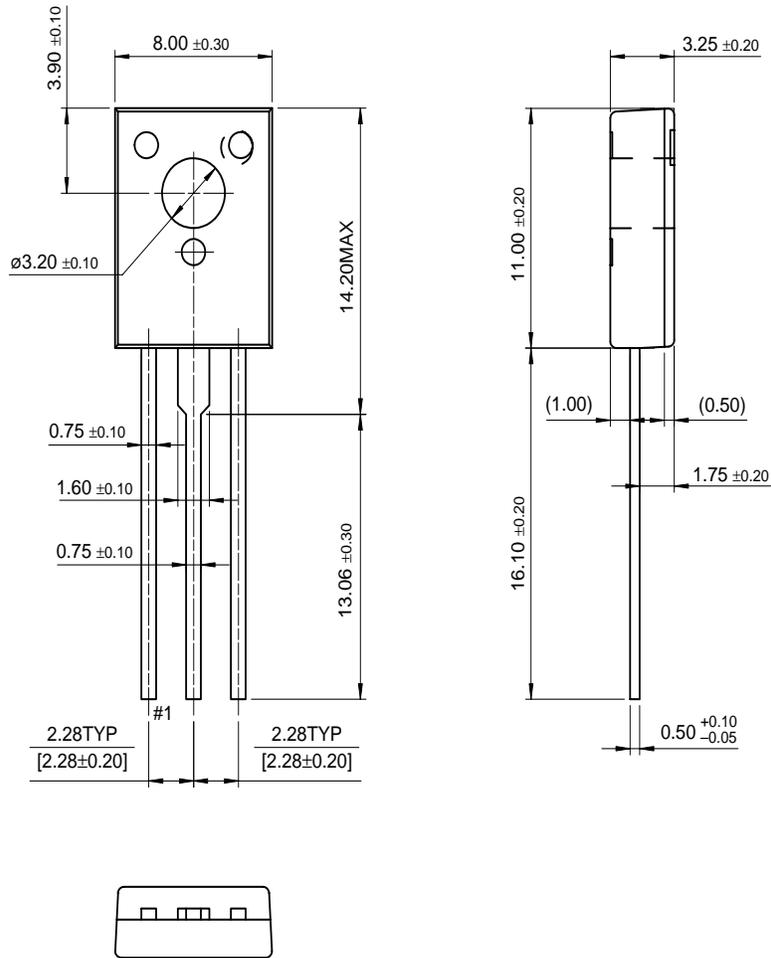


Figure 8. Power Derating

Package Dimensions

KSC2752

TO-126



Dimensions in Millimeters

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| CROSSVOLT™ | POP™ | UHC™ |
| E ² CMOS™ | PowerTrench® | VCX™ |
| FACT™ | QFET™ | |
| FACT Quiet Series™ | QS™ | |
| FAST® | Quiet Series™ | |
| FASTr™ | SuperSOT™-3 | |
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